

- 5.40** Consider an n-type semiconductor at  $T = 300$  K in thermal equilibrium (no current). Assume that the donor concentration varies as  $N_d(x) = N_{d0}e^{-x/L}$  over the range  $0 \leq x \leq L$  where  $N_{d0} = 10^{16} \text{ cm}^{-3}$  and  $L = 10 \text{ } \mu\text{m}$ . (a) Determine the electric field as a function of  $x$  for  $0 \leq x \leq L$ . (b) Calculate the potential difference between  $x = 0$  and  $x = L$  (with the potential at  $x = 0$  being positive with respect to that at  $x = L$ ).

- a) Per (5.42),  $E_x = -\left(\frac{k_B T}{e}\right) \frac{1}{N_d(x)} \frac{dN_d(x)}{dx}$ . Using the given donor concentration  $N_d(x)$  in MKS units, i.e.,  $N_d(x) = 10^{22}e^{-x/L} \text{ m}^{-3}$ , we get

$$\begin{aligned} E_x &= -\left(\frac{1.380649 \times 10^{-23} (300)}{1.602176634 \times 10^{-19}}\right) \frac{1}{10^{22} e^{-x/L}} \frac{d 10^{22} e^{-x/L}}{dx} \\ &= -2.5852 \times 10^{-2} e^{+x/L} e^{-x/L} \left(\frac{-1}{L}\right) = (1) \left(\frac{2.5852 \times 10^{-2}}{10 \times 10^{-6}}\right) \end{aligned}$$

$$\Rightarrow \underline{E_x = 2585.2 \text{ V/m} = 25.852 \text{ V/cm} \quad 0 \leq x \leq L.}$$

- b) By definition,  $V = -\int \vec{E} \cdot d\vec{l}$ . Therefore, the potential difference  $V$  is

$$V = -\int_{x=L}^0 E_x dx = -\int_{x=L}^0 2585.2 dx = -2585.2(0 - L) = 2585.2(10 \times 10^{-6})$$

$$\Rightarrow \underline{V = 0.02585 \text{ V} = 25.85 \text{ mV}.}$$